

# TC55B4256P/J-12,-15,-20

TENTATIVE DATA

262,144 WORD × 4 BIT BiCMOS STATIC RAM

PRELIMINARY

## DESCRIPTION

The TC55B4256P/J is a 1,048,576 bits high speed static random access memory organized as 262,144 words by 4 bits using BiCMOS technology, and operated from a single 5-volt supply. Toshiba's BiCMOS technology and advanced circuit form provide high speed feature.

The TC55B4256P/J has low power feature with device control using Chip Enable ( $\overline{CE}$ ).

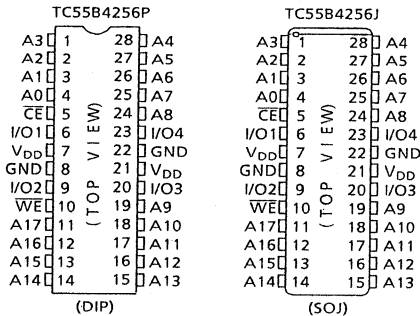
The TC55B4256P/J is suitable for use in various application systems where high speed is required as cache memory, high speed storage, main memory, and so on. All Inputs and Outputs are directly TTL compatible.

The TC55B4256P/J is moulded in 28 pin standard DIP and SOJ with 400 mil width for high density surface assembly.

## FEATURES

- Fast access time :
  - TC55B4256P/J - 12      12ns (MAX.)
  - TC55B4256P/J - 15      15ns (MAX.)
  - TC55B4256P/J - 20      20ns (MAX.)
- Low power dissipation
  - Operation : TC55B4256P/J - 12    130mA (MAX.)
  - TC55B4256P/J - 15    130mA (MAX.)
  - TC55B4256P/J - 20    130mA (MAX.)
  - Standby :                                    10mA (MAX.)
- 5V single power supply : 5V ± 10%
- Fully static operation
- All Inputs and Outputs : TTL compatible
- Package
  - TC55B4256P : DIP28 - P-400A
  - TC55B4256J : SOJ28 - P-400

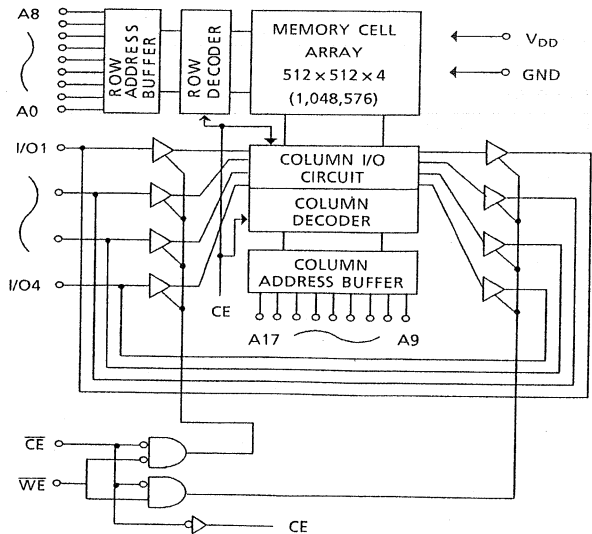
## PIN CONNECTION



## PIN NAMES

A0~A17	Address Inputs
I/O1~I/O4	Data Inputs / Outputs
$\overline{CE}$	Chip Enable Input
$\overline{WE}$	Write Enable Input
V <sub>DD</sub>	Power (+ 5V)
GND	Ground

## BLOCK DIAGRAM



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## MAXIMUM RATINGS

SYMBOL	ITEM	RATING	UNIT
V <sub>DD</sub>	Power Supply Voltage	-0.5~7.0	V
V <sub>IN</sub>	Input Terminal Voltage	-2.0 * ~7.0	V
V <sub>I/O</sub>	I/O Terminal Voltage	-0.5 * ~V <sub>DD</sub> + 0.5	V
P <sub>D</sub>	Power Dissipation	900	mW
T <sub>solder</sub>	Soldering Temperature · Time	260 · 10	°C · sec
T <sub>strg</sub>	Storage Temperature	-65~150	°C
T <sub>opr</sub>	Operating Temperature	-10~85	°C

\* : -3V with a pulse width of 10ns

## DC RECOMMENDED OPERATING CONDITIONS (Ta = 0~70°C)

SYMBOL	PARAMETER	MIN.	TYP.	MAX.	UNIT
V <sub>DD</sub>	Power Supply Voltage	4.5	5.0	5.5	V
V <sub>IH</sub>	Input High Voltage	2.2	-	V <sub>DD</sub> + 0.5	V
V <sub>IL</sub>	Input Low Voltage	-0.5*	-	0.8	V

\* : -3V with a pulse width of 10ns

## DC and OPERATING CHARACTERISTICS (Ta = 0~70°C, V<sub>DD</sub> = 5V ± 10%)

SYMBOL	PARAMETER	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
I <sub>IL</sub>	Input Leakage Current	V <sub>IN</sub> = 0~V <sub>DD</sub>	-	-	± 10	μA
I <sub>OH</sub>	Output High Current	V <sub>OH</sub> = 2.4V	-4	-	-	mA
I <sub>OL</sub>	Output Low Current	V <sub>OL</sub> = 0.4V	8	-	-	mA
I <sub>LO</sub>	Output Leakage Current	$\overline{CE} = V_{IH}$ or $\overline{WE} = V_{IL}$ , V <sub>OUT</sub> = 0~V <sub>DD</sub>	-	-	± 10	μA
I <sub>DDO</sub>	Operating Current	t <sub>cycle</sub> = Min cycle, $\overline{CE} = V_{IL}$ , I <sub>out</sub> = 0mA Other Inputs = V <sub>IH</sub> / V <sub>IL</sub>	-	-	130	mA
I <sub>DDs1</sub>	Standby Current	$\overline{CE} = V_{IH}$ , Other Inputs = V <sub>IH</sub> / V <sub>IL</sub>	-	-	30	mA
I <sub>DDs2</sub>		$\overline{CE} = V_{DD} - 0.2V$ Other Inputs = V <sub>DD</sub> - 0.2V or 0.2V	-	-	10	

CAPACITANCE (Ta = 25°C, f = 1.0MHz)

SYMBOL	PARAMETER	TEST CONDITION	MAX.	UNIT
C <sub>IN</sub>	Input Capacitance	V <sub>IN</sub> = GND	6	pF
C <sub>I/O</sub>	I/O Capacitance	V <sub>I/O</sub> = GND	8	pF

Note : This parameter is periodically sampled and is not 100% tested.

TRUTH TABLE

MODE	$\overline{CE}$	$\overline{WE}$	I/O	POWER
Read	L	H	Dout	I <sub>DDO</sub>
Write	L	L	Din	I <sub>DDO</sub>
Standby	H	*	High - Z	I <sub>DDs</sub>

\* High or Low

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AC CHARACTERISTICS (Ta = 0~70°C<sup>(4)</sup>, V<sub>DD</sub> = 5V ± 10%)

## READ CYCLE

SYMBOL	PARAMETER	TC55B4256P/J – 12		TC55B4256P/J – 15		TC55B4256P/J – 20		UNIT
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
t <sub>RC</sub>	Read Cycle Time	12	–	15	–	20	–	ns
t <sub>ACC</sub>	Address Access Time	–	12	–	15	–	20	
t <sub>CO</sub>	Chip Enable Access Time	–	12	–	15	–	20	
t <sub>COE</sub>	Output Enable Time from $\overline{CE}$	4	–	4	–	4	–	
t <sub>COD</sub>	Output Disable Time from $\overline{CE}$	–	6	–	7	–	8	
t <sub>OH</sub>	Output Data Hold Time from Address Change	4	–	4	–	4	–	
t <sub>PU</sub>	Chip Selection to Power Up Time	0	–	0	–	0	–	
t <sub>PD</sub>	Chip Deselection to Power Down Time	–	12	–	15	–	20	

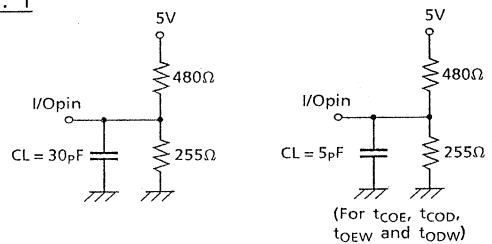
## WRITE CYCLE

SYMBOL	PARAMETER	TC55B4256P/J – 12		TC55B4256P/J – 15		TC55B4256P/J – 20		UNIT
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
t <sub>WC</sub>	Write Cycle Time	12	–	15	–	20	–	ns
t <sub>WP</sub>	Write Pulse Width	8	–	9	–	10	–	
t <sub>AW</sub>	Address Valid to End of Write	9	–	10	–	11	–	
t <sub>CW</sub>	Chip Enable to End of Write	8	–	9	–	10	–	
t <sub>AS</sub>	Address Set Up Time	0	–	0	–	0	–	
t <sub>WR</sub>	Write Recovery Time	1	–	1	–	1	–	
t <sub>OE<sub>W</sub></sub>	Output Enable Time from $\overline{WE}$	1	–	1	–	1	–	
t <sub>OD<sub>W</sub></sub>	Output Disable Time from $\overline{WE}$	–	6	–	7	–	8	
t <sub>DS</sub>	Data Set Up Time	7	–	8	–	9	–	
t <sub>DH</sub>	Data Hold Time	0	–	0	–	0	–	

## AC TEST CONDITIONS

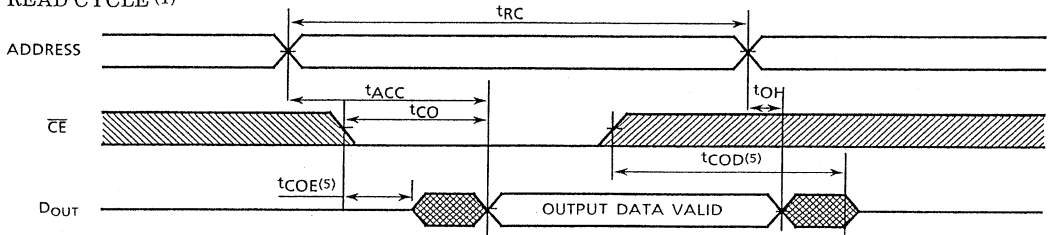
Input Pulse Levels	3.0V/0.0V
Input Pulse Rise and Fall Time	3ns
Input Timing Measurement Reference Levels	1.5V
Output Timing Measurement Reference Levels	1.5V
Output Load	Fig. 1

Fig. 1

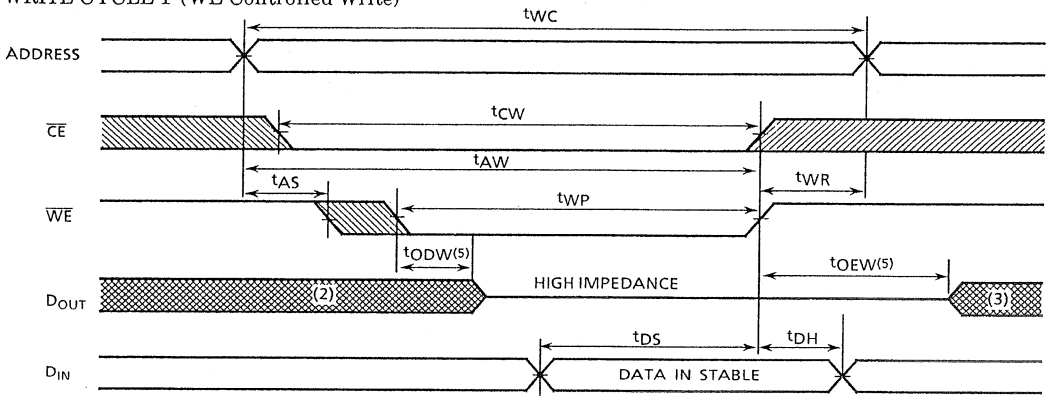


TIMING WAVEFORMS

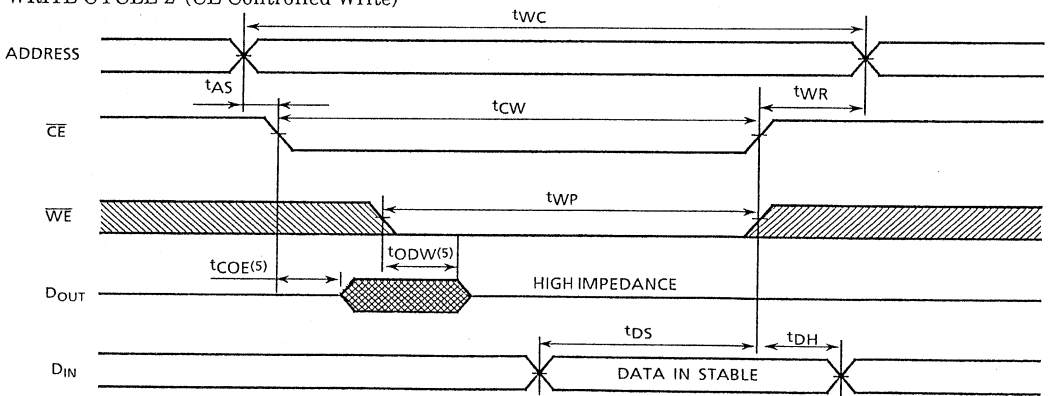
READ CYCLE (1)



WRITE CYCLE 1 ( $\overline{WE}$  Controlled Write)



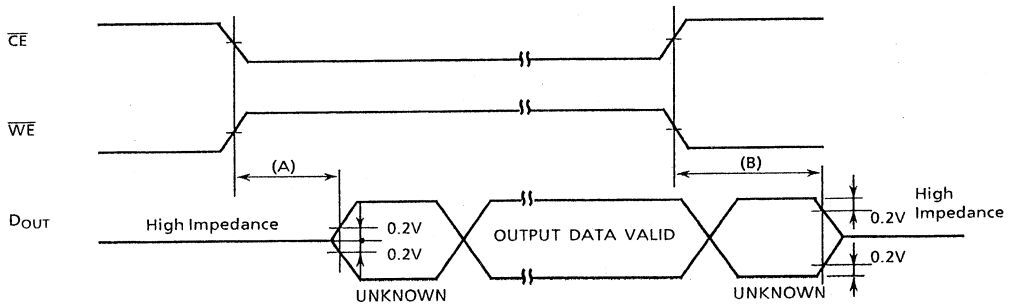
WRITE CYCLE 2 ( $\overline{CE}$  Controlled Write)



Note:

1.  $\overline{WE}$  is High for Read Cycle.
2. Assuming that  $\overline{CE}$  Low transition occurs coincident with or after  $\overline{WE}$  Low transition, outputs remain in a high impedance state.
3. Assuming that  $\overline{CE}$  High transition occurs coincident with or prior to  $\overline{WE}$  High transition, outputs remain in a high impedance state.
4. The Operating temperature ( $T_a$ ) is guaranteed with transverse air flow exceeding 400 linear feet per minute.
5. These parameters are specified as follows and measured by using the load shown in Fig. 1.
 

(A) $t_{COE}, t_{OEw}$	.....	Output Enable Time
(B) $t_{COD}, t_{ODW}$	.....	Output Disable Time



**TOSHIBA**

DATA BOOK

**MOS MEMORY**  
(VRAM, SRAM)

**1991**

# INTRODUCTION

We continually venture at the leading edge of technology so that we may develop and offer to you a diverse array of semiconductor memory products which may be used in many commercial and industrial applications. At this time, we offer three data books; "MOS-Memory Dynamic RAM and Module", "MOS-Memory Video RAM and Static RAM" and "MOS-Memory ROM".

Particularly, this data book is "MOS-Memory Video RAM and Static RAM" edition.

These data books represent our current culminations of electrical characteristics, timing waveforms and package data for our line of semiconductor memory products.

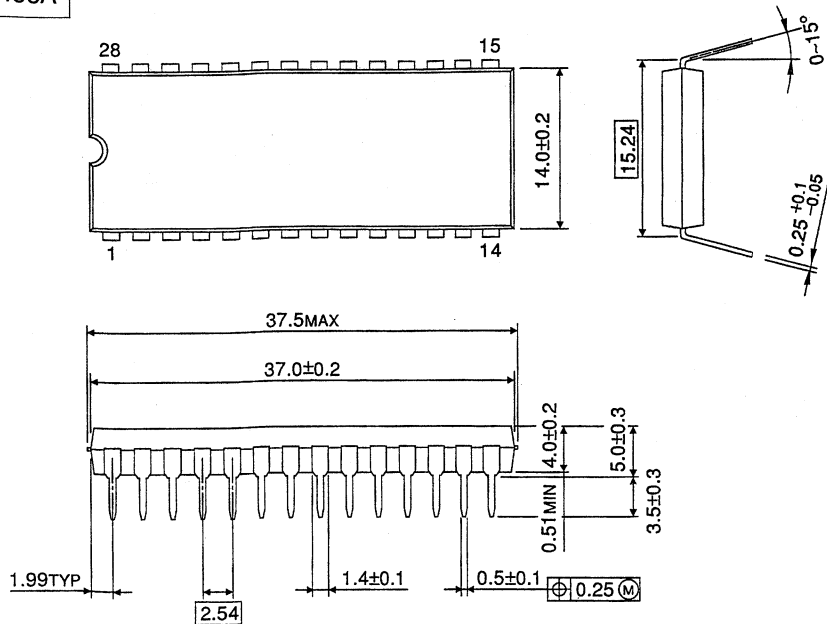
We hope this information will be very useful for you.

Nov. 1991

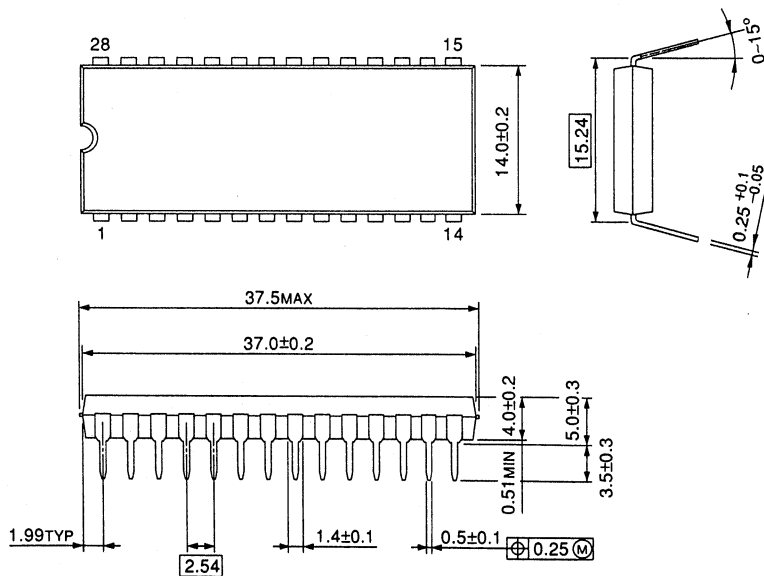
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Semiconductor Group



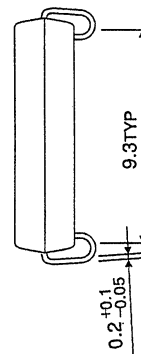
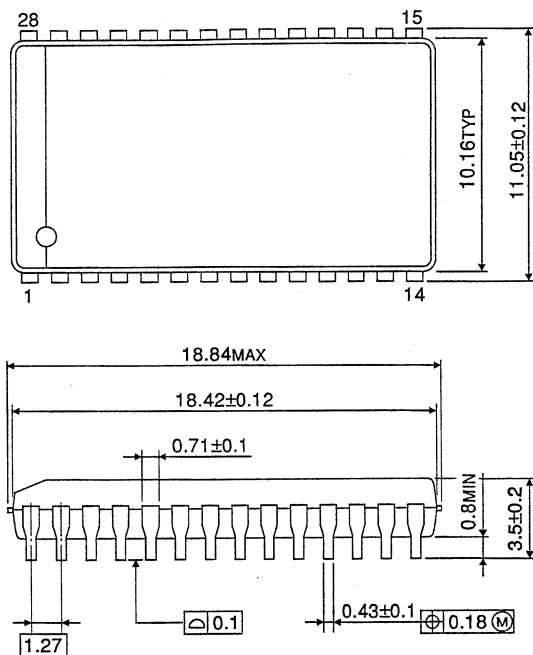
DIP28-P-400A



DIP28-P-600



SOJ28-P-400



SOJ28-P-400A

TENTATIVE

